

Dark matter scattering in dielectrics

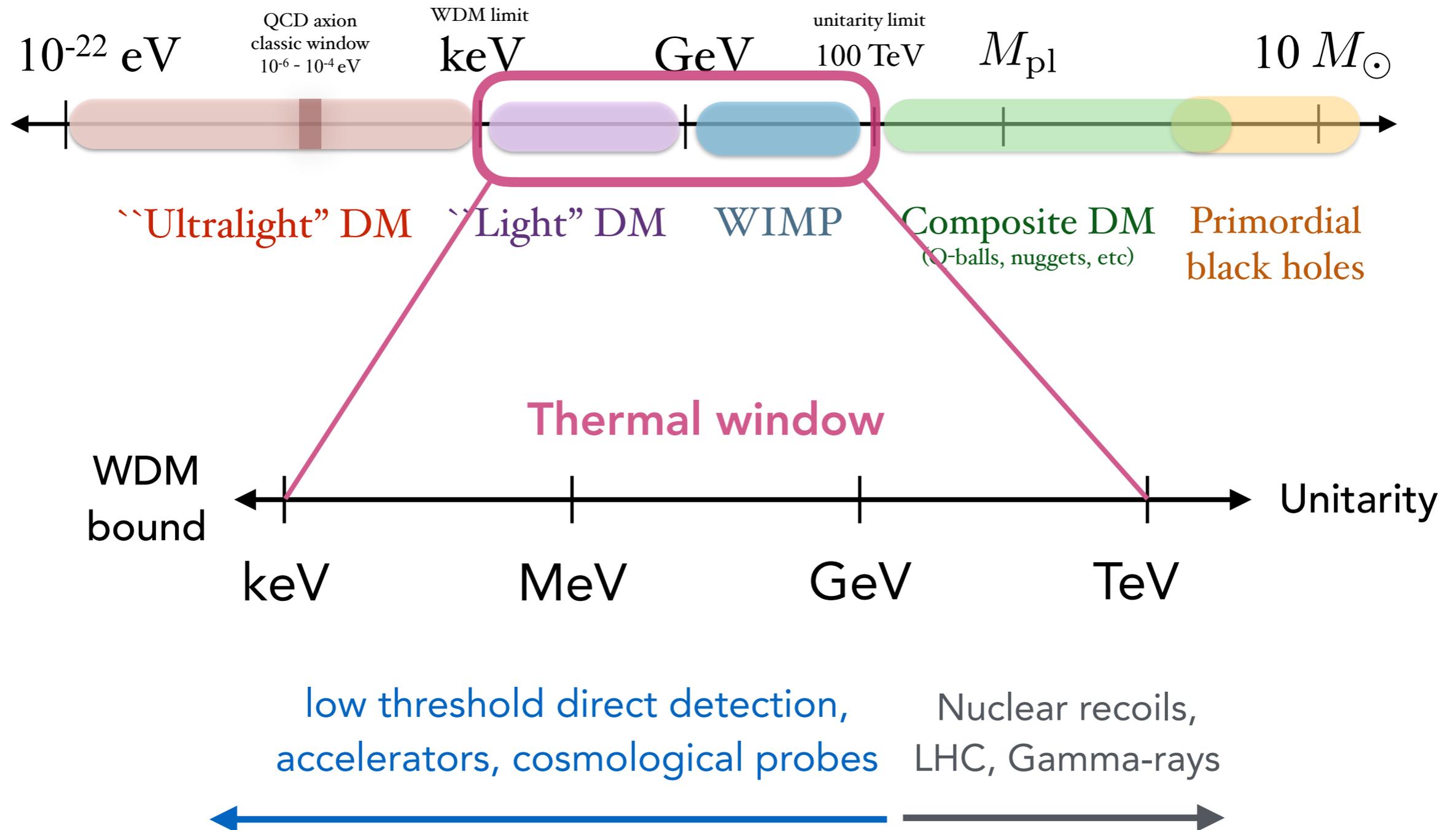
Tongyan Lin
UCSD

March 2, 2021
HiDDeN Webinar

Based on work with Simon Knapen and Jonathan Kozaczuk
2003.12077, 2011.09496, 2101.08275

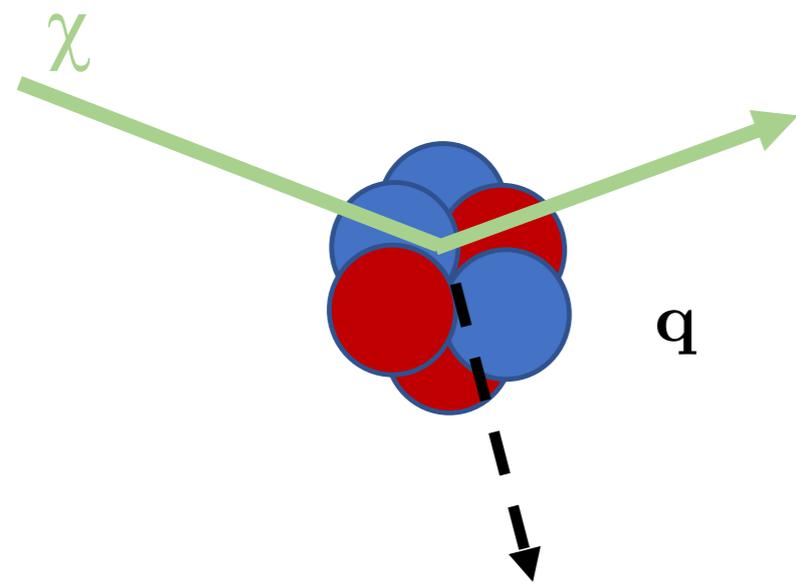
Mass scale of dark matter

(not to scale)



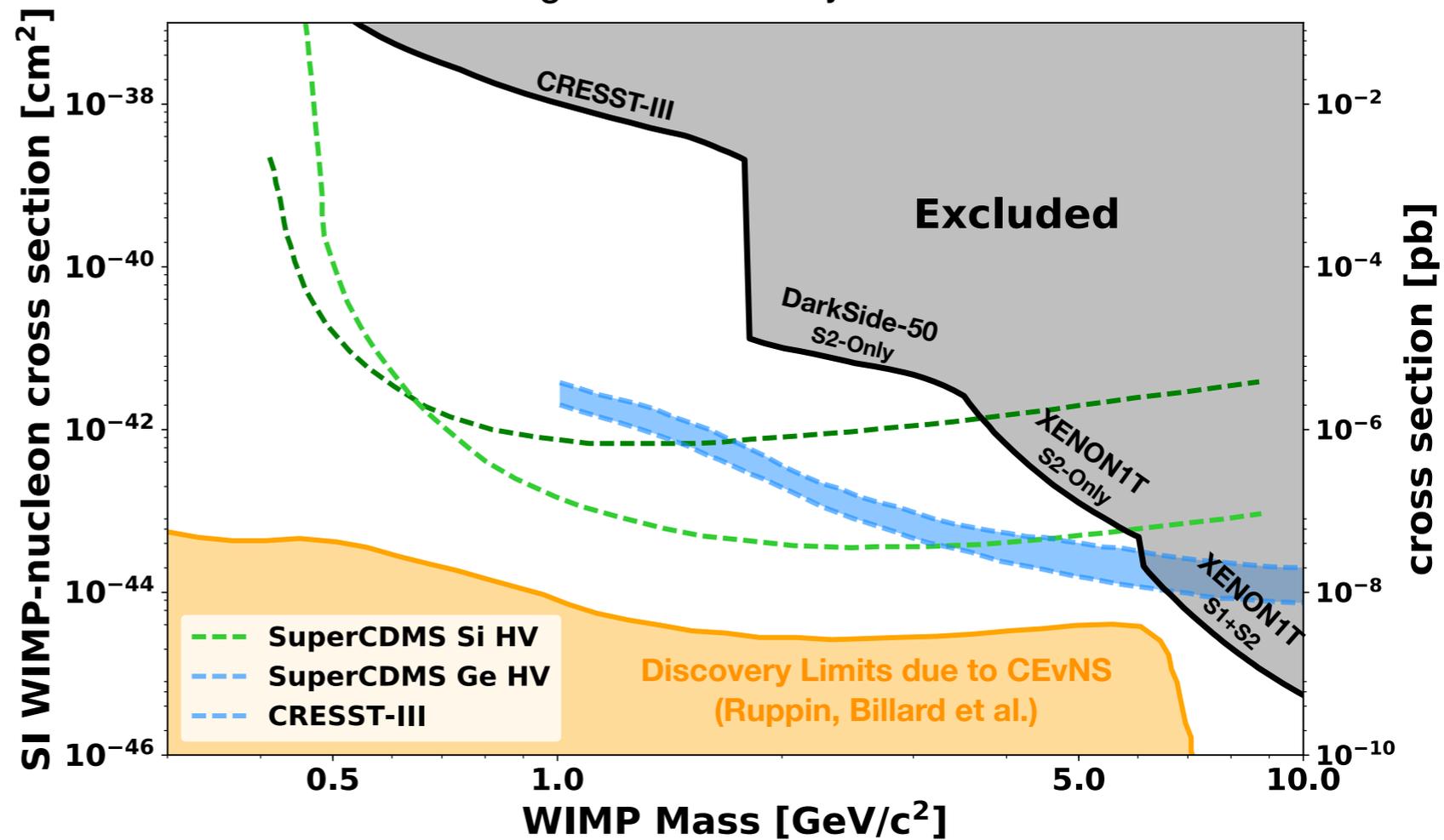
Detecting sub-GeV dark matter

Traditional approach to direct detection of dark matter: DM-nucleus scattering

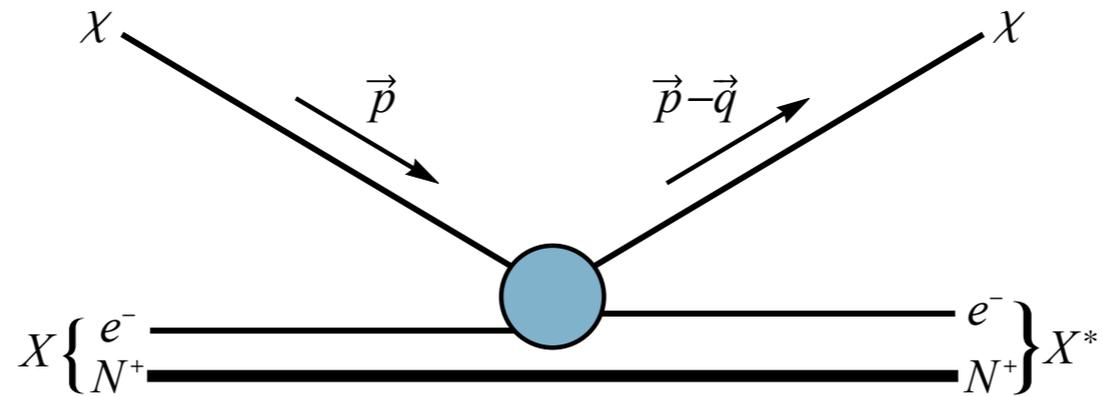


$$E_{NR} \leq \frac{2m_\chi^2 v^2}{m_N} \text{ for sub-GeV DM}$$

Figure from talk by Kaixuan Ni at DPF 2019



Electron recoils



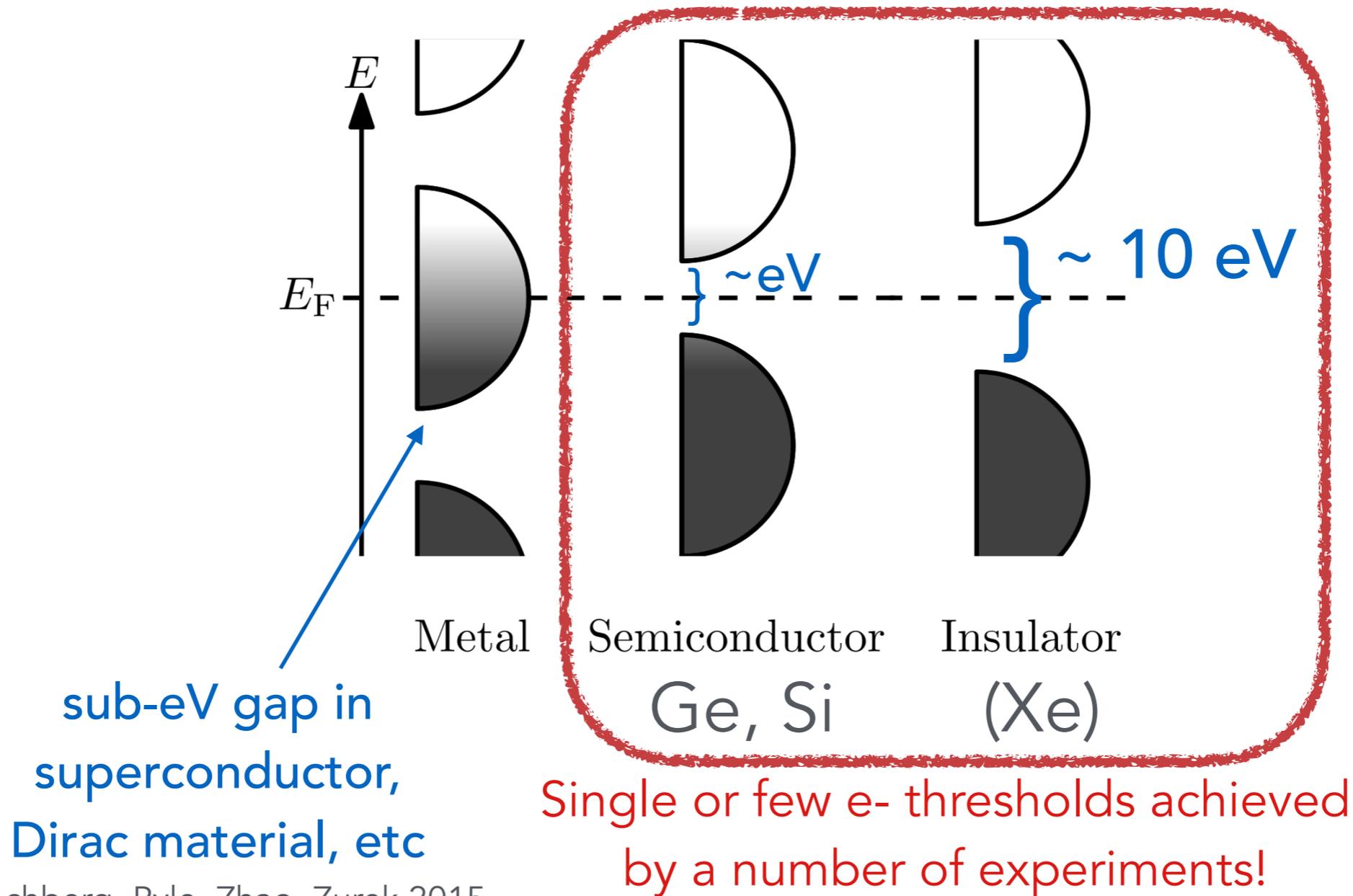
e- in materials are not free or isolated particles

Opportunity: constrained by available energy eigenstates rather than free-particle kinematics.

Complication: need to know eigenstates and wavefunctions in a many-body system.

Opportunity: constrained by available energy eigenstates rather than free-particle kinematics.

Electronic band structure



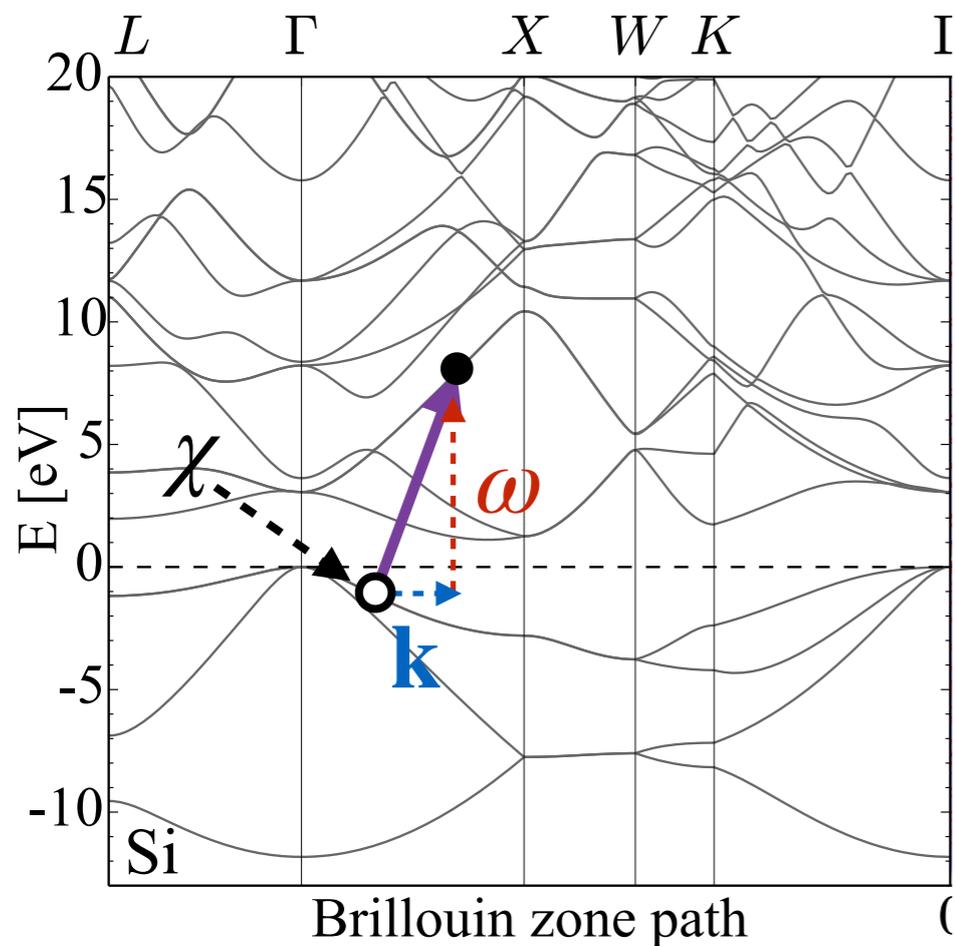
Single or few e- thresholds achieved by a number of experiments!

[Hochberg, Pyle, Zhao, Zurek 2015
Dirac: 1708.08929, 1910.02091, etc]

[DAMIC, SENSEI, SuperCDMS]

Complication: need to know eigenstates and wavefunctions in a many-body system.

Semiconductor target



Rate to create electron-hole pairs:

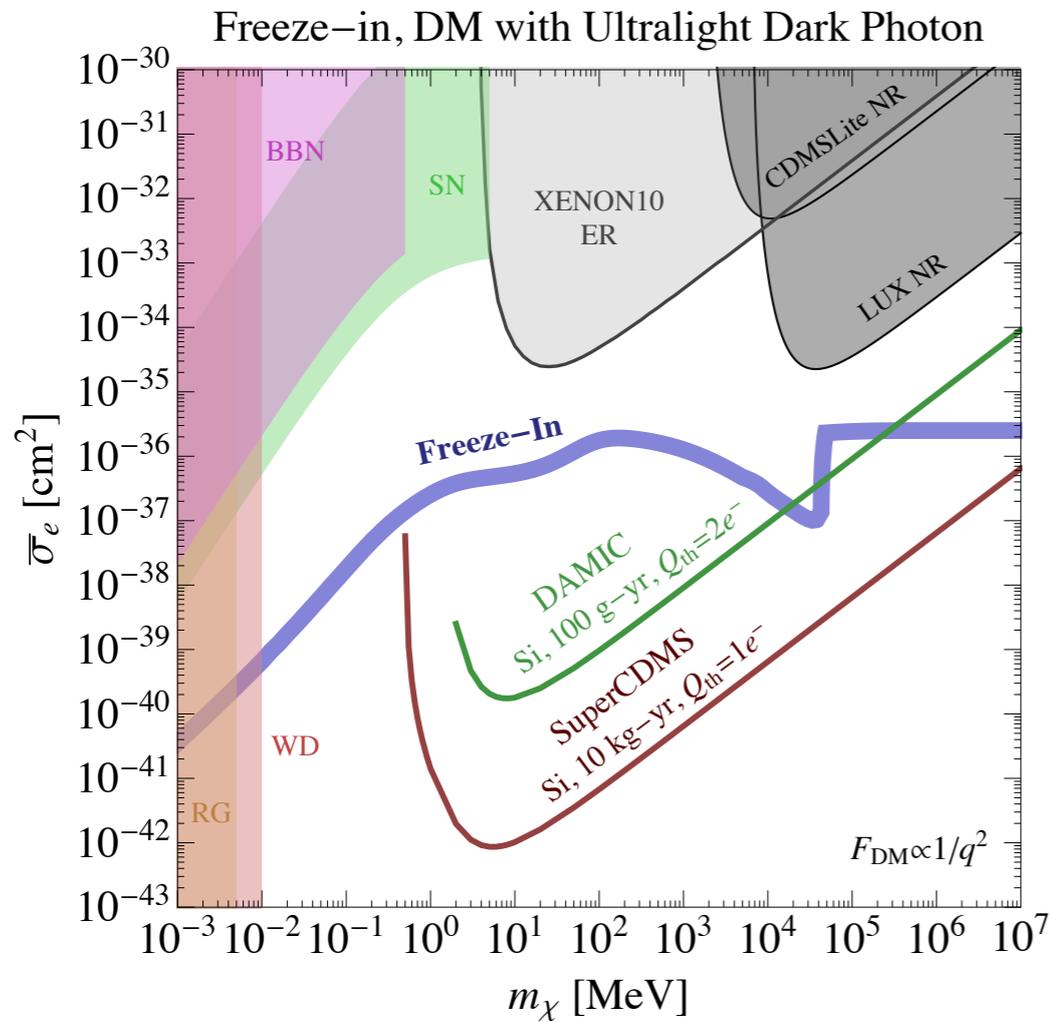
Wavefunction overlap

$$\frac{d\sigma}{d^3\mathbf{k}d\omega} \propto \bar{\sigma}_e F_{\text{med}}^2(k) \sum_{\ell, \ell'} \sum_{\mathbf{p}, \mathbf{p}'} \overbrace{|\langle \mathbf{p}', \ell' | e^{i\mathbf{k}\cdot\mathbf{r}} | \mathbf{p}, \ell \rangle|^2}^{\text{Wavefunction overlap}} \times f^0(\omega_{\mathbf{p}, \ell}) (1 - f^0(\omega_{\mathbf{p}', \ell'})) \delta(\omega + \omega_{\mathbf{p}, \ell} - \omega_{\mathbf{p}', \ell'})$$

Sum over occupied bands ℓ and Bloch momentum \mathbf{p} to excited state $|\mathbf{p}', \ell'\rangle$

Essig, Mardon, Volansky 2011;
Essig, Fernandez-Serra, Mardon,
Soto, Volansky, Yu 2015

Semiconductor target



Plot from Essig, Fernandez-Serra, Mardon, Soto, Volansky, Yu 2015

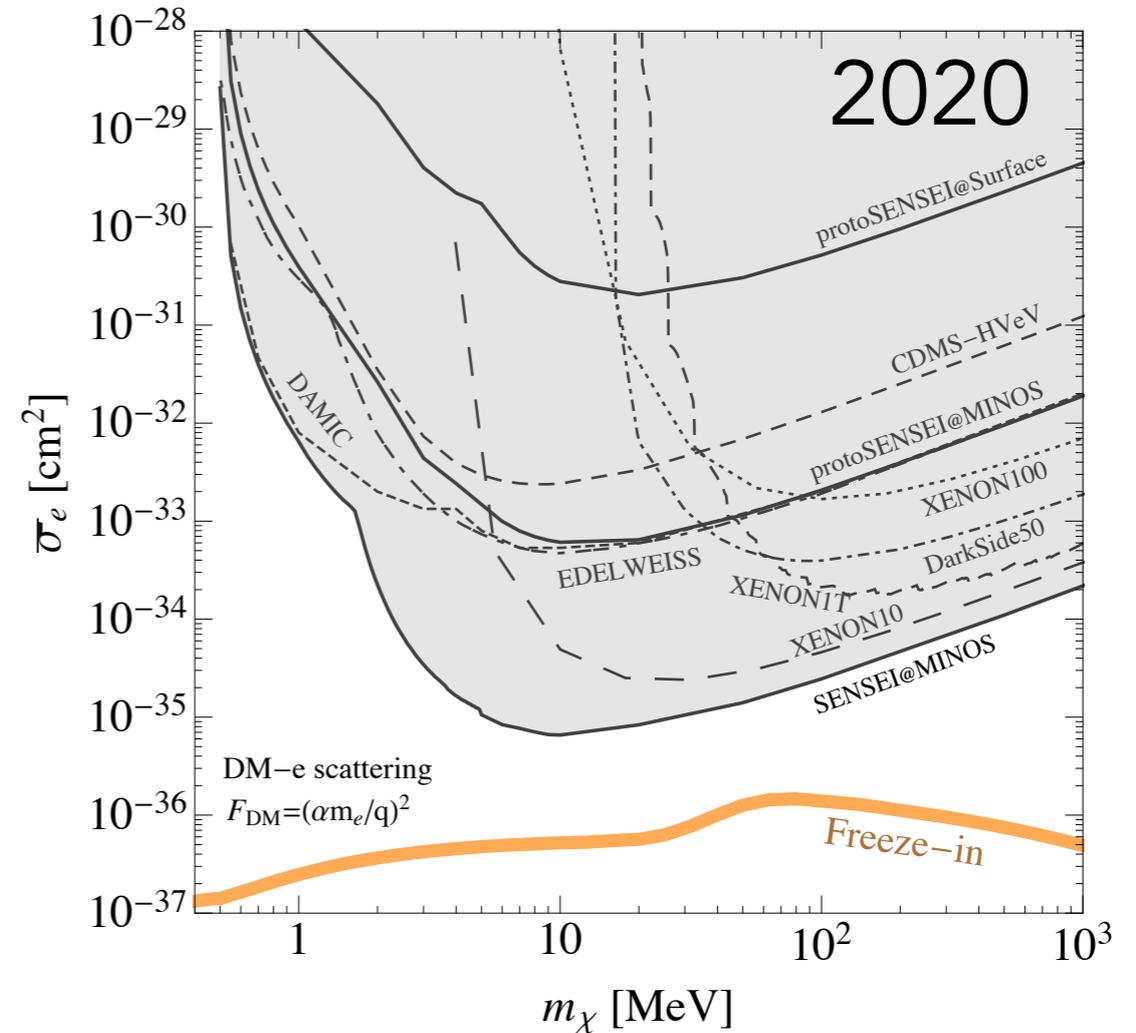
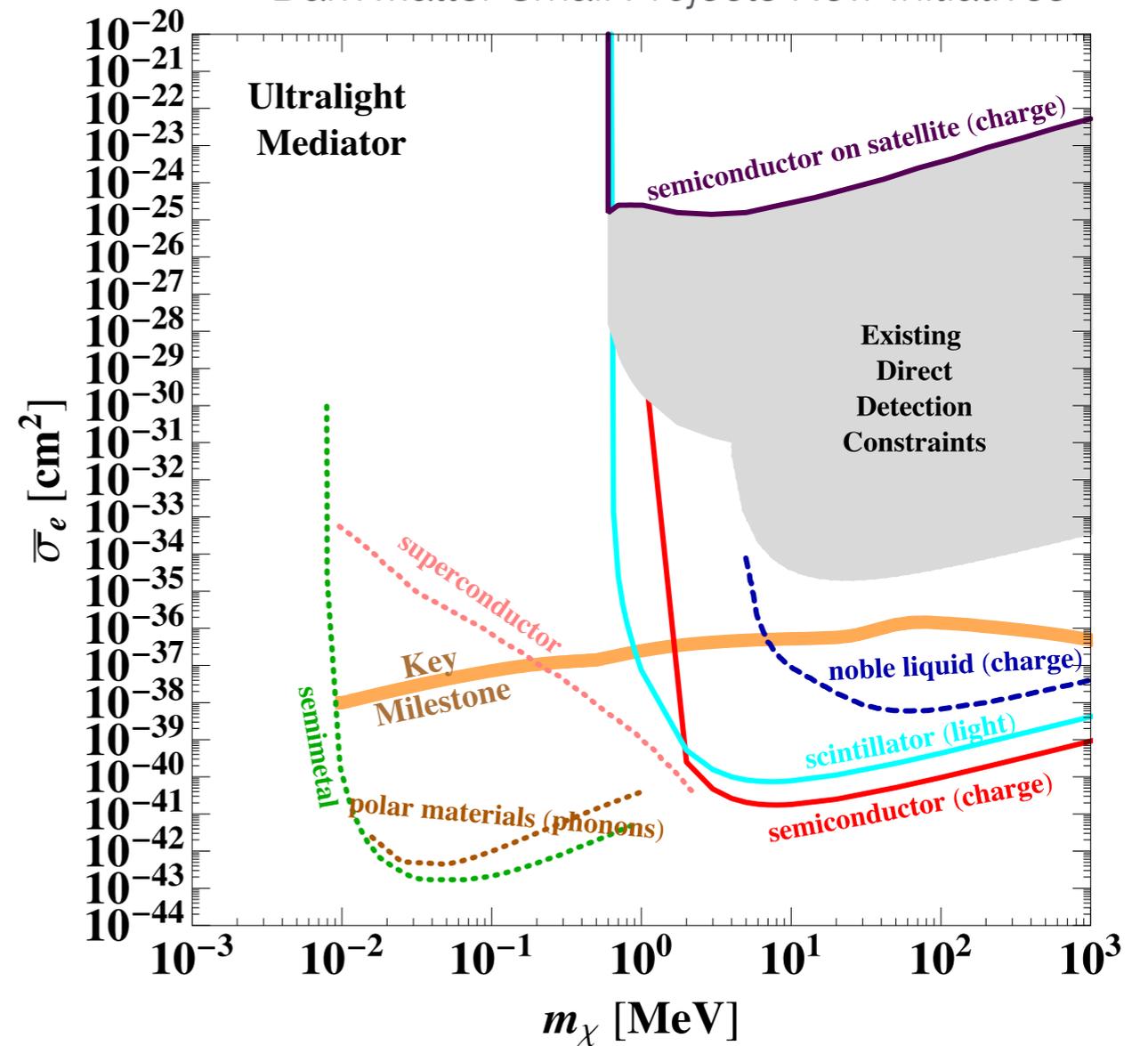


Figure from talk by Rouven Essig

From Basic Research Needs Report:
 "Dark Matter Small Projects New Initiatives"

Now many papers studying
 different targets, proposed
 experiments, and new
 experiments in development.

All dielectrics



Today: how to think about DM scattering in all these materials in terms of dielectric response, and how that led us to identify and calculate new effects.

Outline

Dark matter scattering as dielectric response

Implications for DM-electron scattering

The Migdal effect in semiconductors

Linear response

Dielectric response

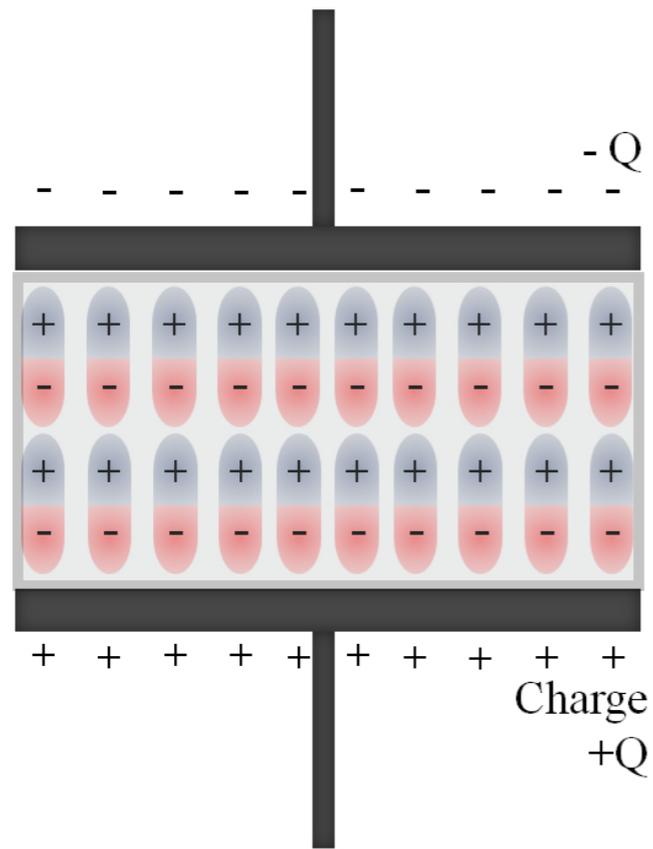
$\epsilon^{-1}(\omega, \mathbf{k})$ — response of E fields*

Susceptibility

$\chi(\omega, \mathbf{k})$ — response of electron number density

* Some technicalities: consider only longitudinal response; neglect crystal periodicity

Dielectric response



$$\nabla \cdot \mathbf{E} = \frac{4\pi \rho_{\text{ext}}}{\epsilon}$$

$$\mathbf{E} = \frac{\mathbf{E}_{\text{ext}}}{\epsilon}$$

More generally:

$$\mathbf{E}(\mathbf{r}, \omega) = \int d^3 \mathbf{r}' \epsilon^{-1}(\mathbf{r}, \mathbf{r}', \omega) \mathbf{E}_{\text{ext}}(\mathbf{r}', \omega)$$

$$\mathbf{E}(\omega, \mathbf{k}) = \epsilon^{-1}(\omega, \mathbf{k}) \mathbf{E}_{\text{ext}}(\omega, \mathbf{k})$$

Susceptibility

Induced charge density*: $\rho_{\text{ind}} = \frac{\rho_{\text{ext}}}{\epsilon} - \rho_{\text{ext}}$

Linear response to a perturbation:

$$H = -en(\mathbf{r})\Phi_{\text{ext}}(\mathbf{r}) = -e \int d^3\mathbf{k} n_{-\mathbf{k}} \frac{4\pi\rho_{\text{ext}}(\mathbf{k})}{k^2}$$

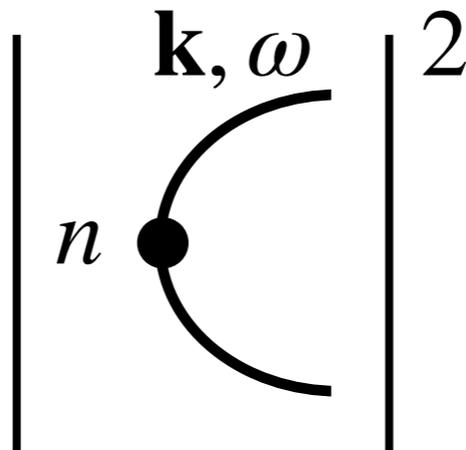
$$\rho_{\text{ind}} = -en_{\text{ind}} = \chi \frac{4\pi e^2}{k^2} \rho_{\text{ext}}$$

$$\chi(\omega, \mathbf{k}) = \frac{-i}{V} \int_0^\infty dt e^{i\omega t} \langle [n_{\mathbf{k}}(t), n_{-\mathbf{k}}(0)] \rangle$$

* Assume dominated by electrons

Induced charge is related to amount of screening:

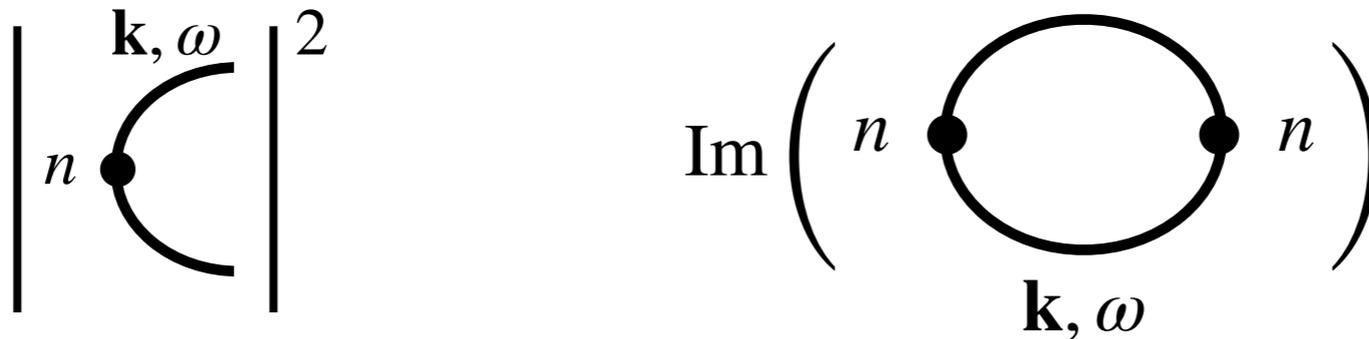
$$\frac{1}{\epsilon(\omega, \mathbf{k})} = 1 + \frac{4\pi e^2}{k^2} \chi(\omega, \mathbf{k})$$

$$H = -en(\mathbf{r}) \Phi_{\text{ext}}(\mathbf{r}) \quad \left| \begin{array}{c} \mathbf{k}, \omega \\ n \end{array} \right|^2$$


Fluctuation-dissipation [Optical] theorem

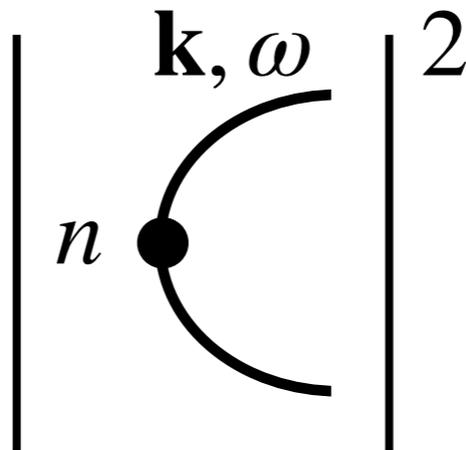
Spectrum of
fluctuations

$$S(\omega, \mathbf{k}) = \frac{2}{(1 - e^{-\beta\omega})} \text{Im}(-\chi(\omega, \mathbf{k})) \quad \text{Dissipation}$$

$$\left| \begin{array}{c} \mathbf{k}, \omega \\ n \end{array} \right|^2 \quad \text{Im} \left(n \begin{array}{c} \circlearrowleft \\ \mathbf{k}, \omega \end{array} n \right)$$


Induced charge is related to amount of screening:

$$\frac{1}{\epsilon(\omega, \mathbf{k})} = 1 + \frac{4\pi e^2}{k^2} \chi(\omega, \mathbf{k})$$

$$H = -en(\mathbf{r}) \Phi_{\text{ext}}(\mathbf{r}) \quad \left| \begin{array}{c} \mathbf{k}, \omega \\ n \end{array} \right|^2$$


The diagram shows a particle (represented by a black dot) inside a potential well (represented by a curved line). The particle is labeled 'n'. The well is labeled with 'k, ω' above it and a superscript '2' to the right of the well's opening.

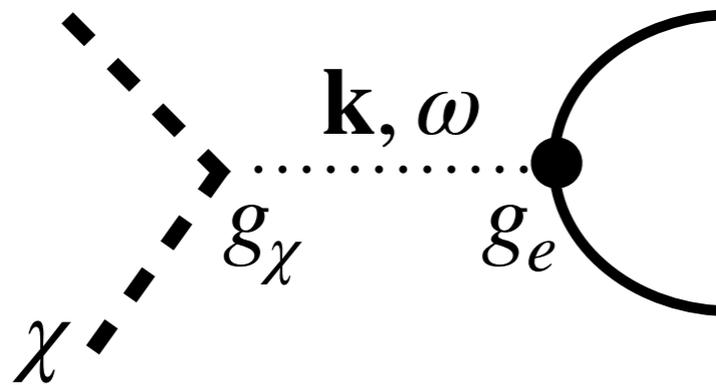
Fluctuation-dissipation [Optical] theorem

$$S(\omega, \mathbf{k}) = \frac{2}{(1 - e^{-\beta\omega})} \text{Im}(-\chi(\omega, \mathbf{k}))$$

$$= \frac{k^2}{2\pi\alpha_{em}(1 - e^{-\beta\omega})} \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

Energy Loss Function (ELF)

DM-electron scattering



$$H = -e \int d^3\mathbf{k} n_{\mathbf{k}} \frac{g_{\chi} g_e e^{i\mathbf{k}\cdot\mathbf{r}}}{k^2 + m_V^2}$$

$$\frac{d\sigma}{d^3\mathbf{k}d\omega} \propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) S(\omega, \mathbf{k}) \propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

Charge
fluctuations

Energy Loss
Function (ELF)

- Implications
- 1. Screening effects for vector and scalar mediators
 - 2. Many approaches to calculate or measure ϵ

$$\frac{d\sigma}{d^3\mathbf{k}d\omega} \propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

$$\propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) \frac{\text{Im} \epsilon(\omega, \mathbf{k})}{|\epsilon(\omega, \mathbf{k})|^2}$$

Proportional to DM-electron scattering form factor in the independent-electron approximation (RPA)

$$\text{Im} \epsilon^{\text{RPA}}(\omega, \mathbf{k}) = \frac{4\pi^2 \alpha_{em}}{V k^2} \sum_{\ell, \ell'} \sum_{\mathbf{p}, \mathbf{p}'} |\langle \mathbf{p}', \ell' | e^{i\mathbf{k}\cdot\mathbf{r}} | \mathbf{p}, \ell \rangle|^2 \times f^0(\omega_{\mathbf{p}, \ell}) (1 - f^0(\omega_{\mathbf{p}', \ell'})) \delta(\omega + \omega_{\mathbf{p}, \ell} - \omega_{\mathbf{p}', \ell'})$$

$|\epsilon(\omega, \mathbf{k})|^2$ screening for vector mediators considered in superconductors, Dirac materials.

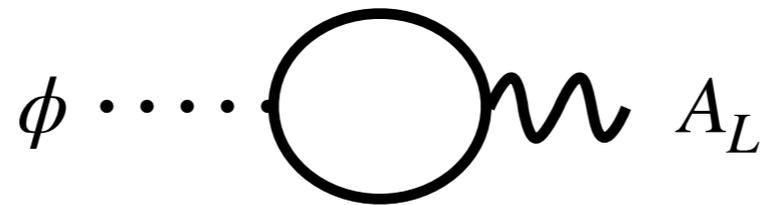
Not included in signal rates for semiconductors. Assumed to be absent for scalar mediators.

Screening of scalars

Interaction basis: $g_e \phi \bar{e} e$

Mixing of scalar mediator with SM photon?

In-medium
mixing



$$\Pi_{\phi A} = \frac{g_e}{e} \Pi_{AA}^{0\mu} \epsilon_{\mu}^L$$

In-medium scattering amplitude

In the non-relativistic limit:

$$\sim \frac{1}{\epsilon(\omega, \mathbf{k})} \frac{g_{\chi} g_e}{k^2 + m_{\phi}^2}$$

Vector and scalar mediators

$$-\mathcal{L} \supset g_\chi \phi \bar{\chi} \chi + g_e \phi \bar{e} e \quad \rightarrow g_\chi \phi n_\chi + g_e \phi n$$

$$-\mathcal{L} \supset g_\chi V_\mu \bar{\chi} \gamma^\mu \chi + g_e V_\mu \bar{e} \gamma^\mu e \quad \rightarrow g_\chi V_0 n_\chi + g_e V_0 n$$

Non-relativistic scattering ($k \gg \omega$) is dominated by scattering through Yukawa potential

$$H = -e \int d^3\mathbf{k} n_{\mathbf{k}} \frac{g_\chi g_e e^{i\mathbf{k}\cdot\mathbf{r}}}{k^2 + m_V^2}$$

DM-electron scattering via vector or scalar mediators is identical in the nonrelativistic limit

The energy loss function (ELF)

$$\text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

Theory

Many established approaches to ϵ

Include local field effects

Include electron-electron interactions

Experiment

Optical measurements

X-ray scattering

Fast electron scattering (EELS)

See Kurinsky, Baxter, Kahn, Krnjaic 2020 and Hochberg, Kahn, Kurinsky, Lehmann, Yu, and Berggren 2021 for complementary work and more emphasis on experimental calibration of dielectric function

Understanding the ELF and implications for DM-electron scattering

The dielectric function

Random-phase approximation (RPA):

Emission – absorption

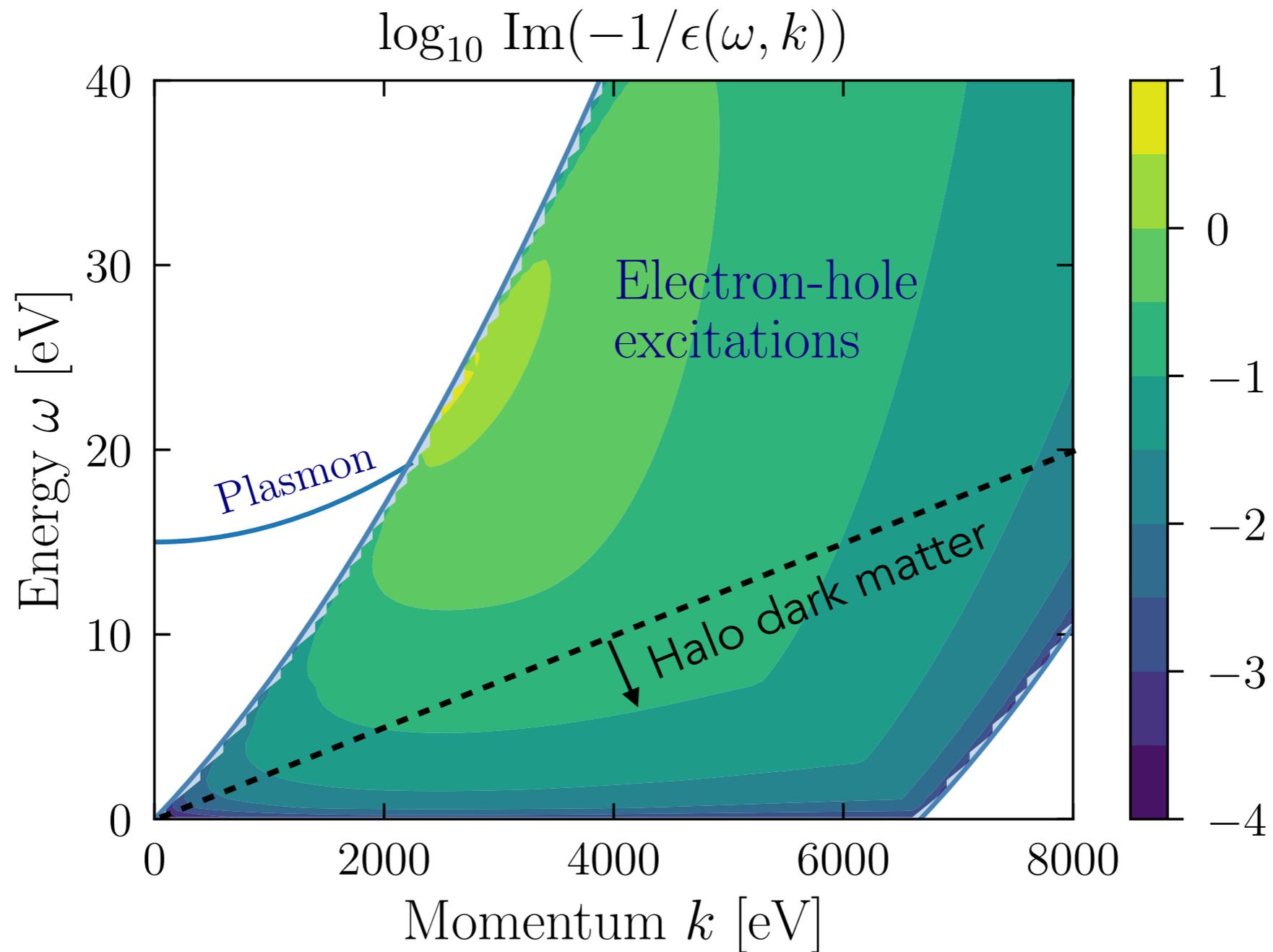
$$\epsilon^{\text{RPA}}(\omega, \mathbf{k}) = 1 + \frac{4\pi\alpha_{em}}{Vk^2} \lim_{\eta \rightarrow 0} \underbrace{\sum_{\ell, \ell'} \sum_{\mathbf{p}, \mathbf{p}'} |\langle \mathbf{p}', \ell' | e^{i\mathbf{k} \cdot \mathbf{r}} | \mathbf{p}, \ell \rangle|^2 \frac{f^0(\omega_{\mathbf{p}', \ell'}) - f^0(\omega_{\mathbf{p}, \ell})}{\omega + \omega_{\mathbf{p}, \ell} - \omega_{\mathbf{p}', \ell'} + i\eta}}_{\text{Leading order polarization assuming independent electron response}}$$

Leading order polarization assuming independent electron response

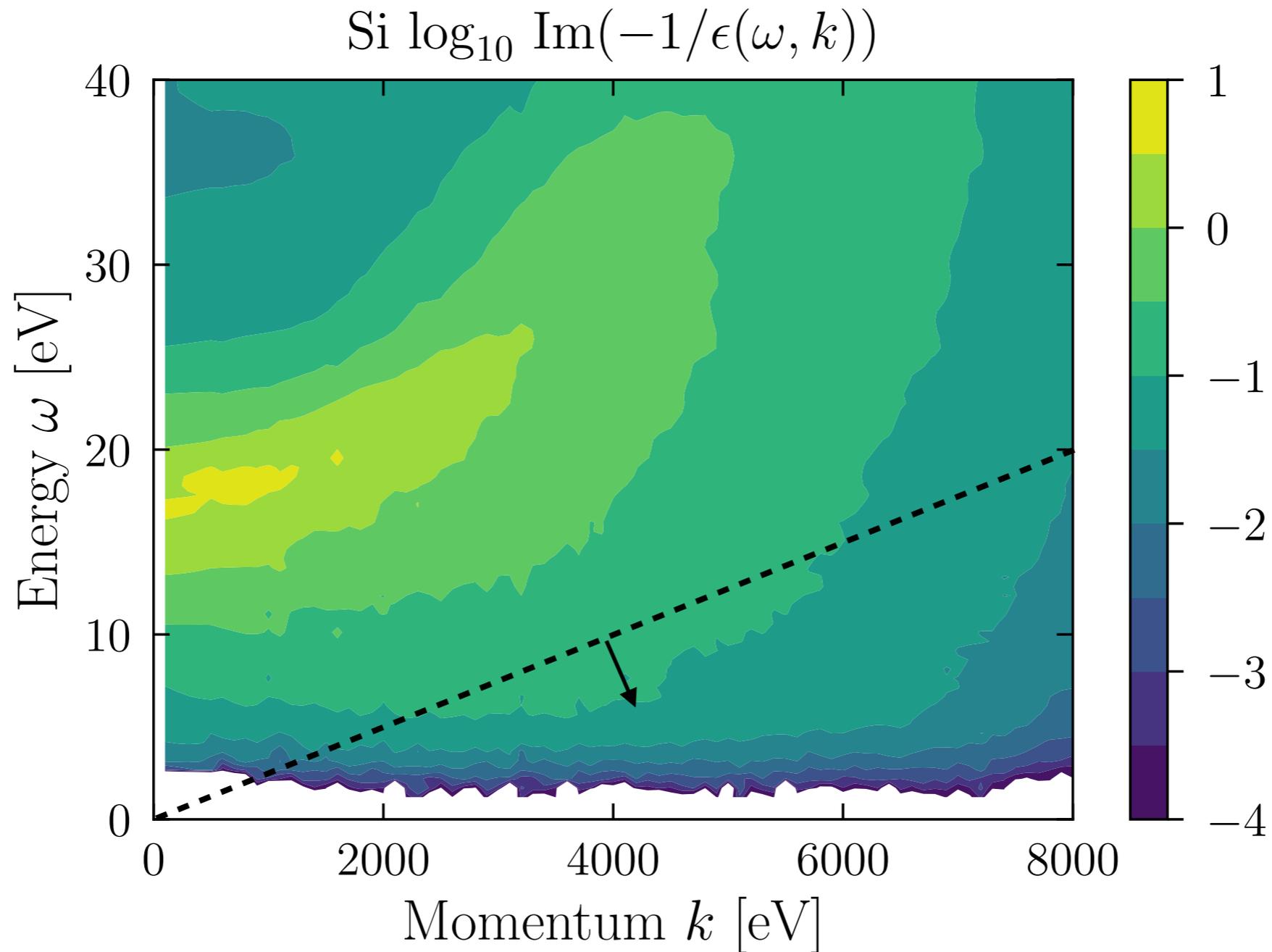
Can be evaluated analytically in free degenerate electron gas with

Fermi momentum p_F and plasma frequency $\omega_p = \sqrt{4\pi\alpha_{em}n_e/m_e}$

Electron gas model

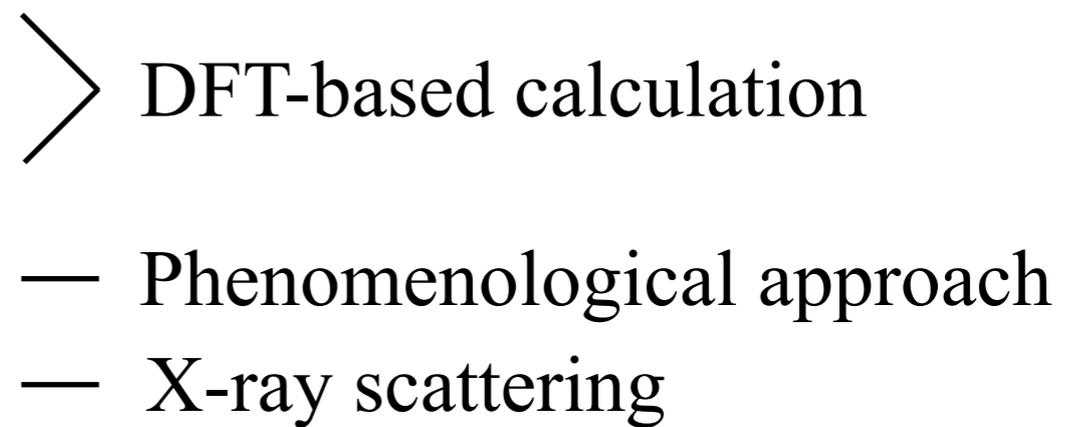
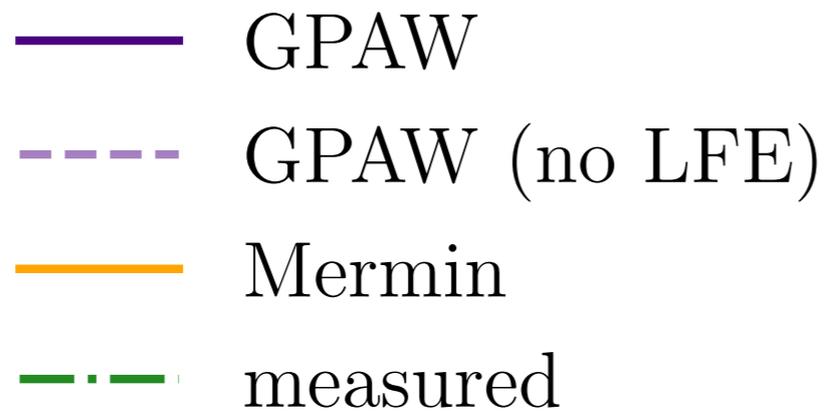
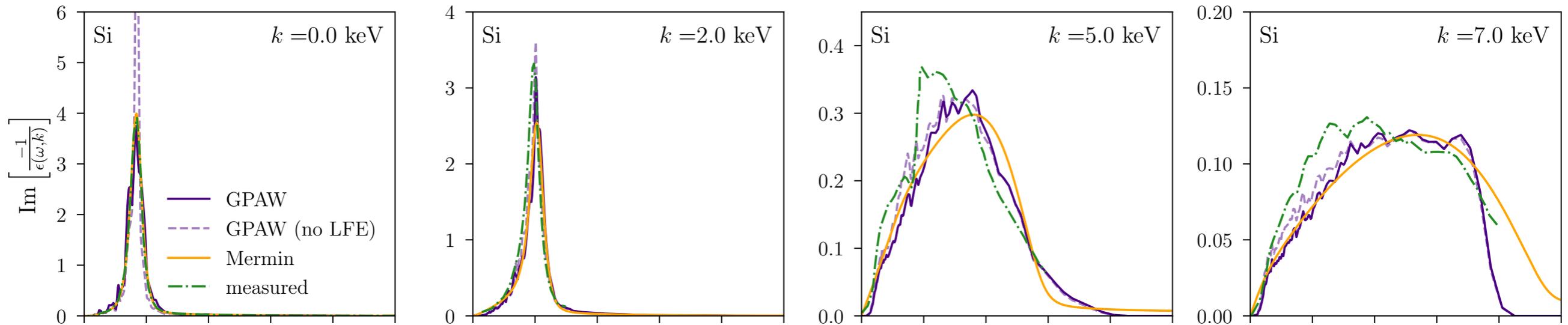


ELF in semiconductors



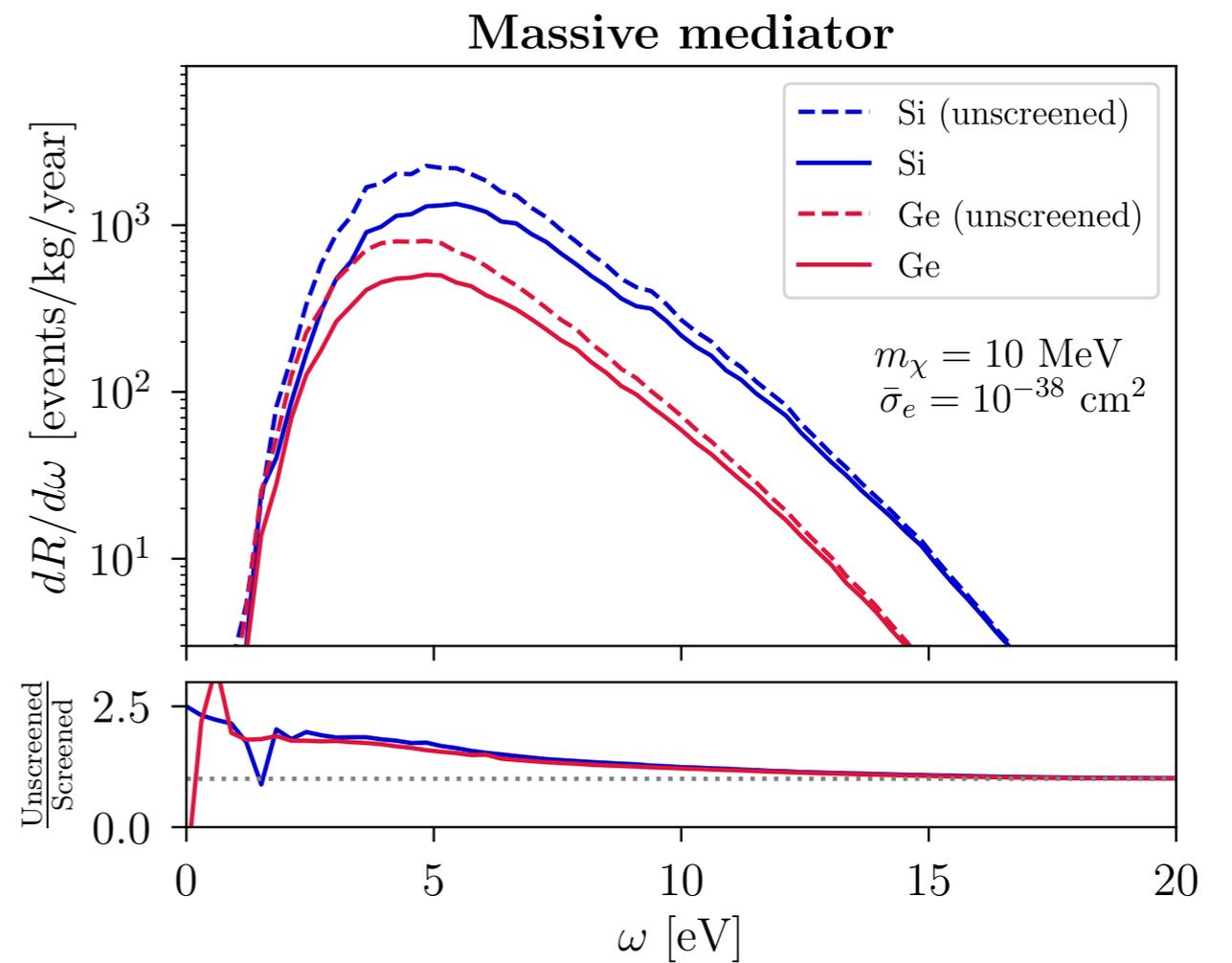
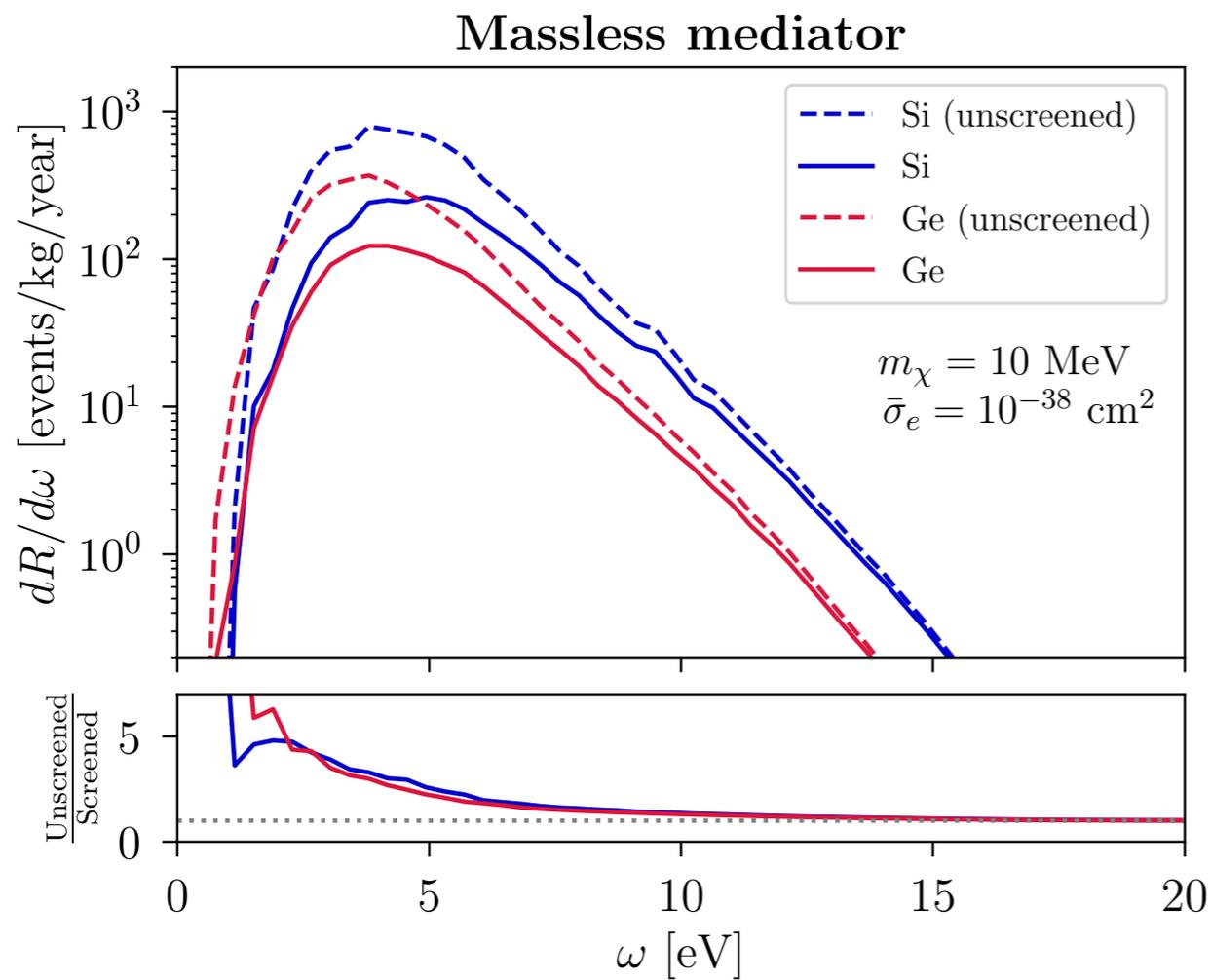
Density function theory (DFT) calculation using GPAW

ELF in Silicon



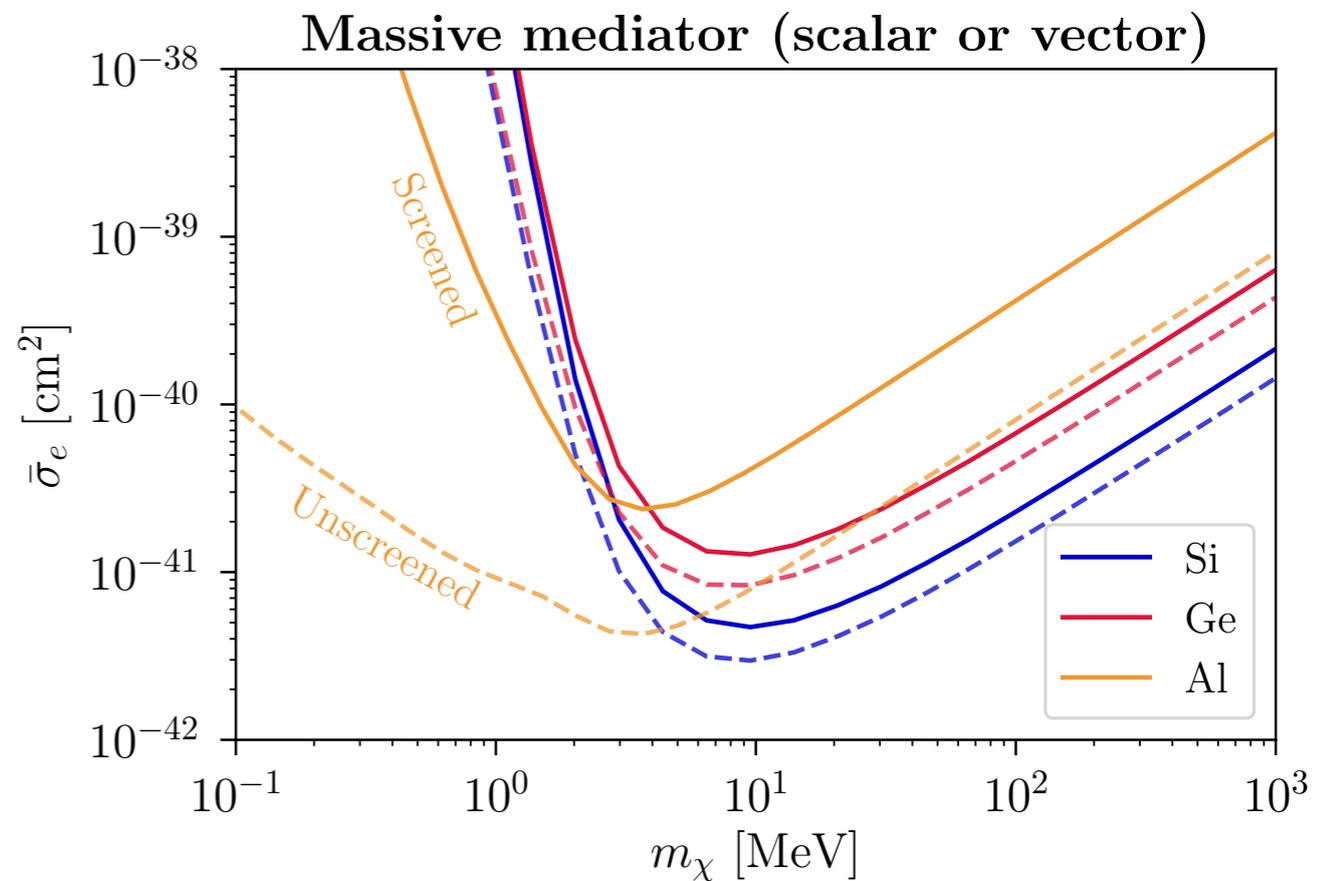
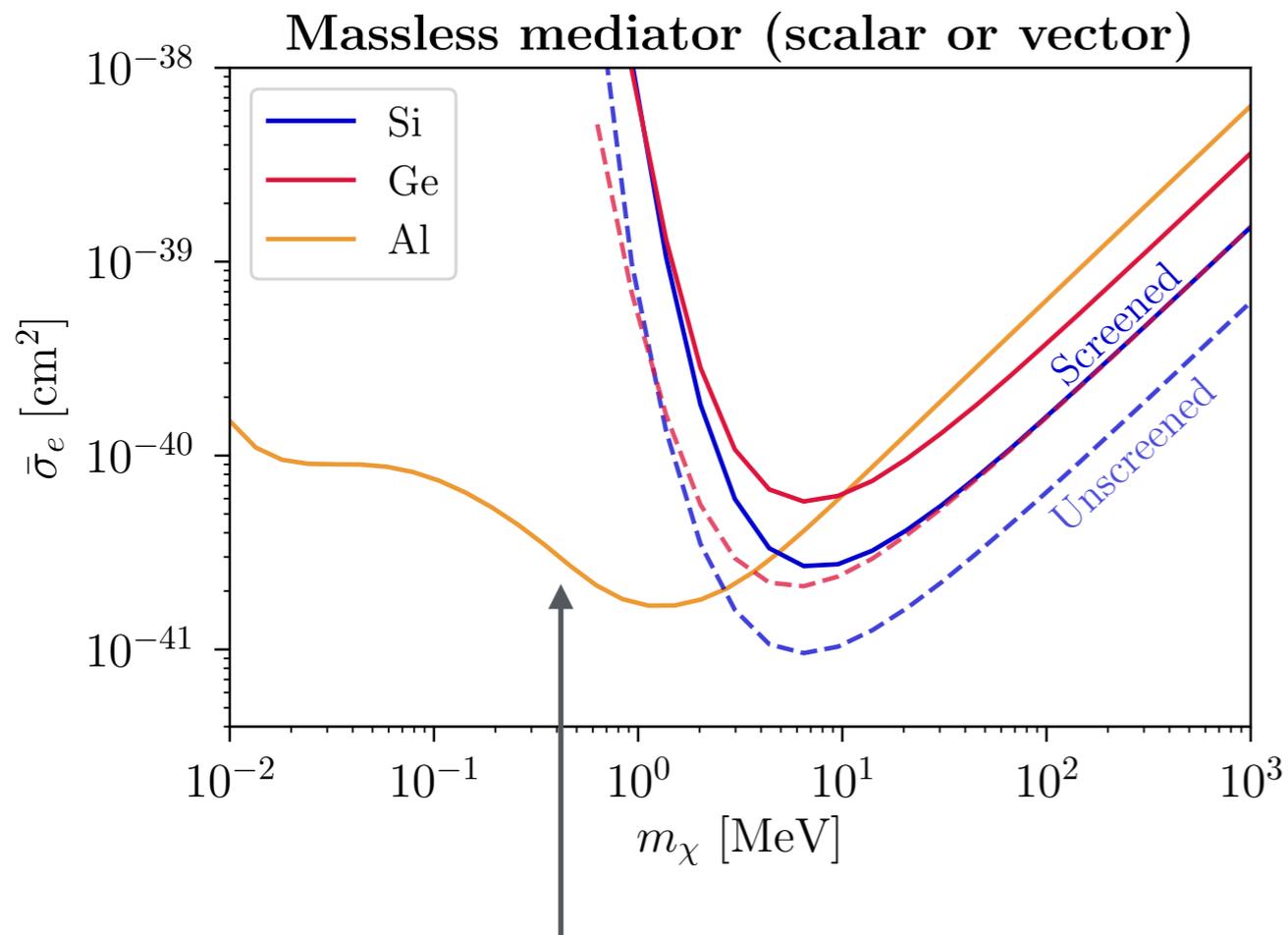
GPAW: Mortensen, Hansen, Jacobsen 2005;
 Enkovaara, Rostgaard, Morstensen + 2010;
 Mermin approach: Vos and Grande 2021
 X-ray: Weissker et al. 2010

Implications for DM-electron scattering



Unscreened: $\text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right) \rightarrow \text{Im} (\epsilon(\omega, \mathbf{k}))$

Implications for DM-electron scattering



Metal/superconductor: large screening, but also massive gains in rate at low momentum

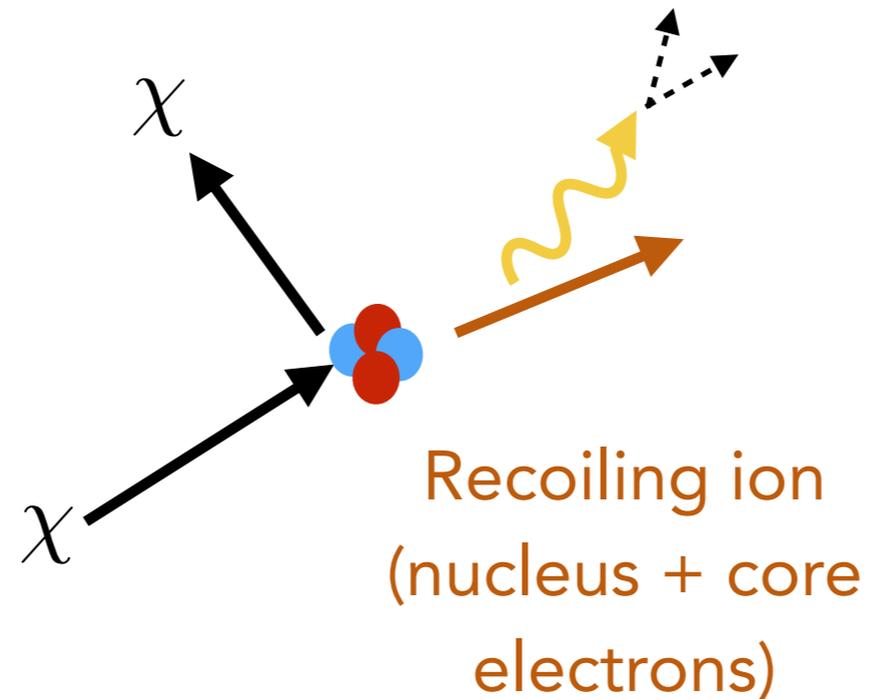
Summary

$$\frac{d\sigma}{d^3\mathbf{k}d\omega} \propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

DM-electron scattering is determined by the energy loss function (ELF)

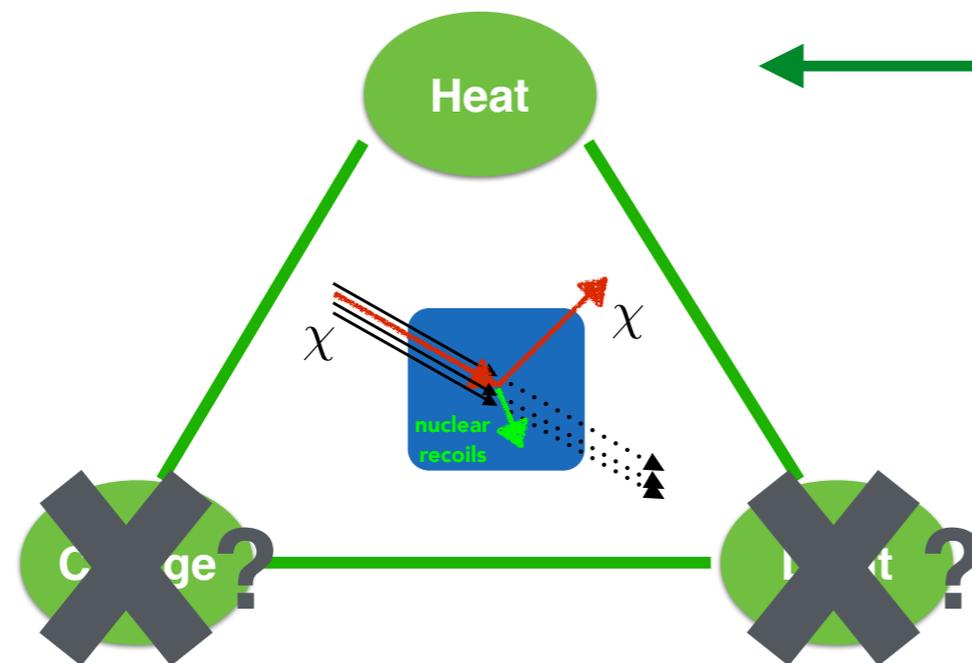
Account for screening effects (scalar and vector mediators) and many-body physics to desired accuracy. Effects in semiconductors impact sensitivity of current/upcoming experiments

The Migdal effect in semiconductors



with Simon Knapen and Jonathan Kozaczk
2011.09496, 2101.08275

Challenges of low-energy nuclear recoils



Search for rare inelastic processes where electron recoil accompanies nuclear recoil

Lower the heat threshold

- Detectors in development to reach ~eV scale thresholds and lower
- Search for single phonon excitations with sub-eV thresholds

- Bremsstrahlung $\chi + N \rightarrow \chi + N + \gamma$
- Migdal effect $\chi + N \rightarrow \chi + N + e^-$

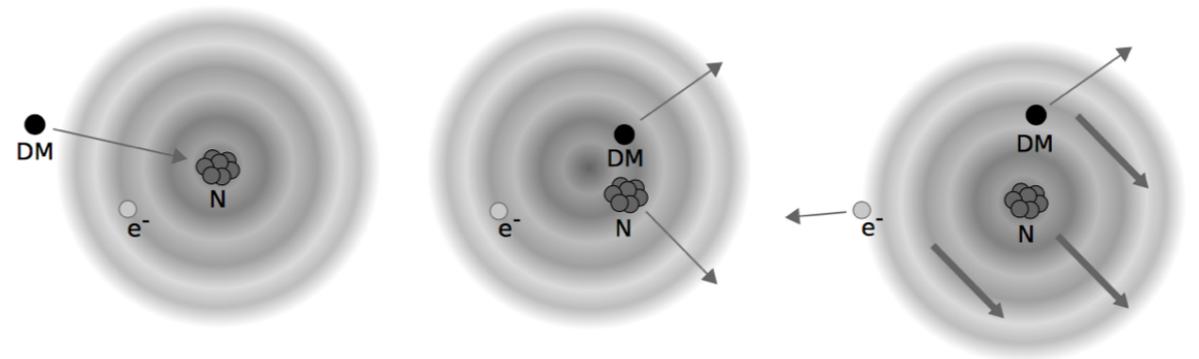
Atomic Migdal effect

Electrons have to 'catch up' to recoiling nucleus

Boost initial state to frame of moving nucleus:

$$|i\rangle \rightarrow e^{im_e \mathbf{v}_N \cdot \sum_{\beta} \mathbf{r}_{\beta}} |i\rangle$$

From 1711.09906 (Dolan, Kahlhoefer, McCabe)



Transition probability $|\mathcal{M}_{if}|^2$

$$\mathcal{M}_{if} = \langle f | e^{im_e \mathbf{v}_N \cdot \sum_{\beta} \mathbf{r}_{\beta}} | i \rangle \approx im_e \langle f | \mathbf{v}_N \cdot \sum_{\beta} \mathbf{r}_{\beta} | i \rangle$$

Nucleus recoils with velocity \mathbf{v}_N

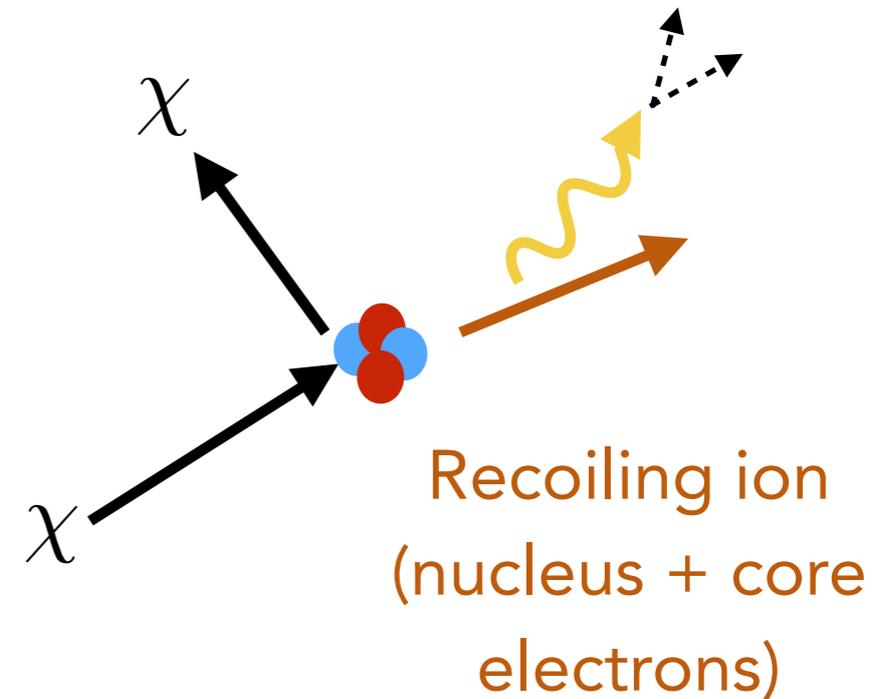
Small probability for "shake-off" electron, but allows low-energy nuclear recoil to be above the e- recoil threshold

The Migdal effect as bremsstrahlung

Bremsstrahlung calculation



treating N as nucleus with tightly bound core electrons. Valid for $10 \text{ MeV} \lesssim m_\chi \lesssim 1 \text{ GeV}$.



Usual DM-nucleus scattering

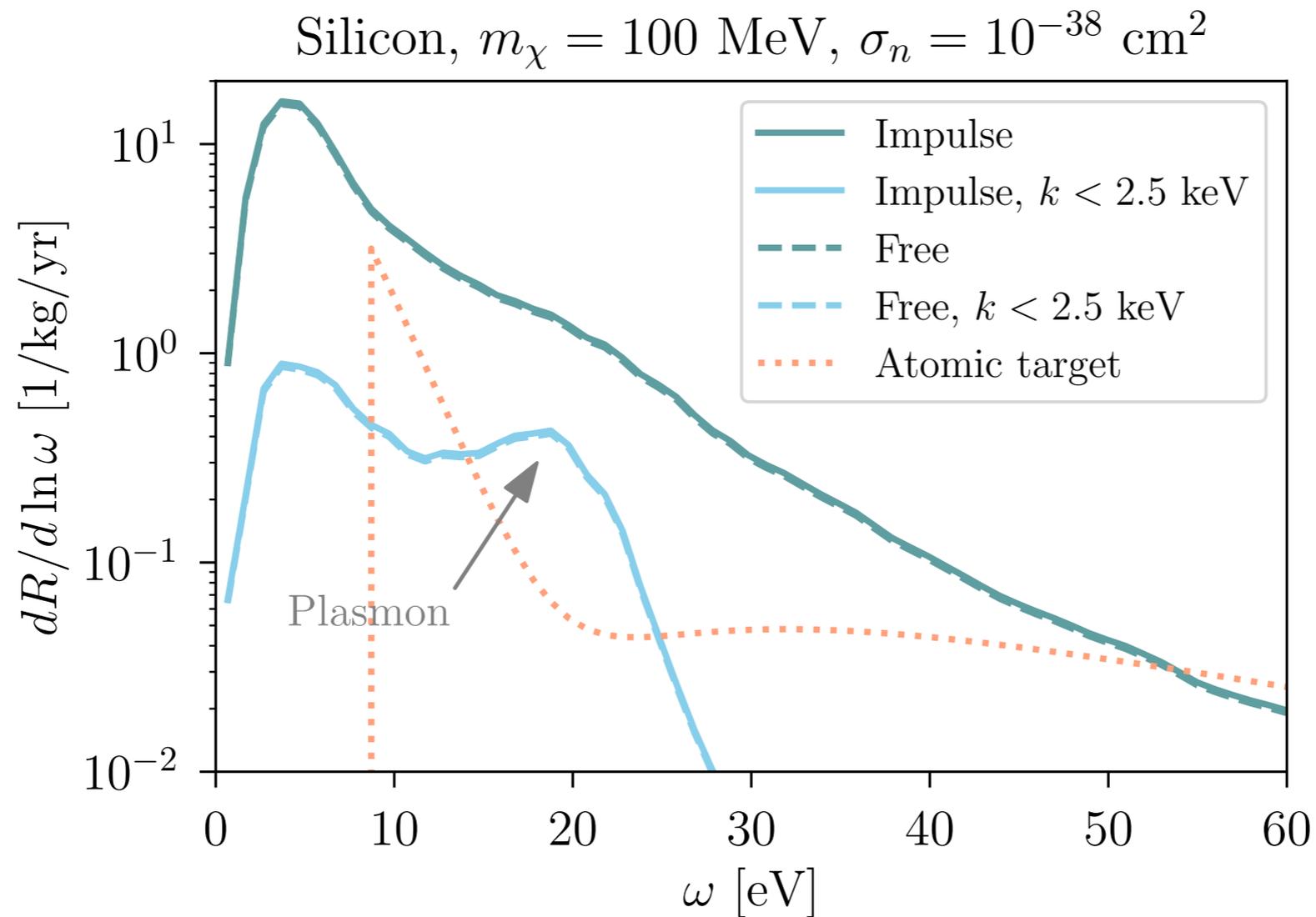
$$\frac{d\sigma}{d\omega} = \frac{2\pi^2 A^2 \sigma_n}{m_\chi^2 v_\chi} \int \frac{d^3 \mathbf{q}_N}{(2\pi)^3} \int \frac{d^3 \mathbf{p}_f}{(2\pi)^3} \delta(E_i - E_f - \omega - E_N) \times \int \frac{d^3 \mathbf{k}}{(2\pi)^3} F(\mathbf{p}_i - \mathbf{p}_f - \mathbf{q}_N - \mathbf{k})^2$$

$$\times 4\alpha_{em} Z_{\text{ion}}^2 \left[\frac{1}{\omega - \mathbf{q}_N \cdot \mathbf{k} / m_N} - \frac{1}{\omega} \right]^2 \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

Form factor accounting for multiphonon response in a harmonic crystal

Differential probability of ion to excite an electron

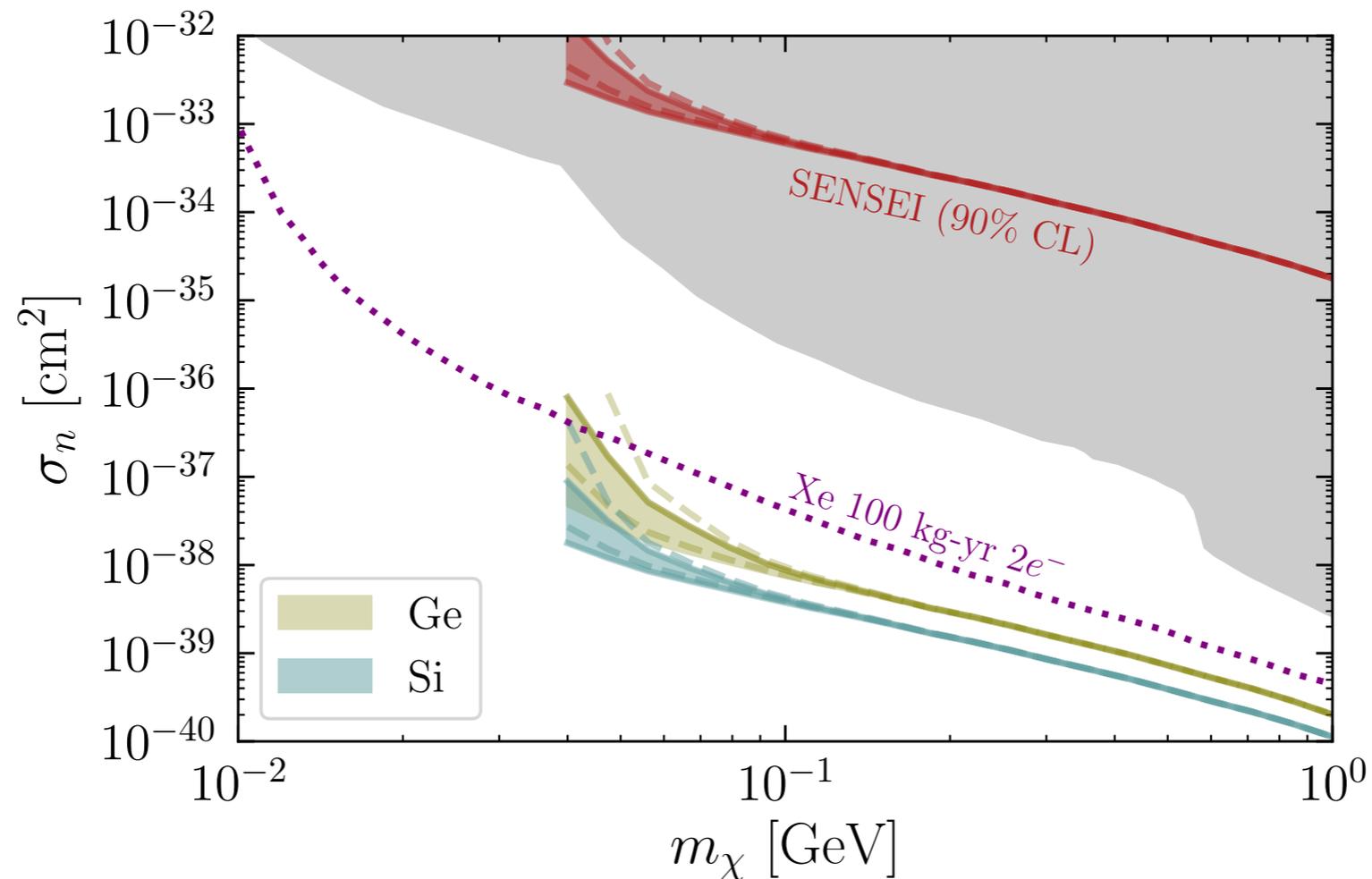
Full rate in semiconductors



Rate in semiconductors is much larger due to lower gap for excitations.

Sensitivity in semiconductors

1 kg-year exposure, with $\Omega > 2$ (similar to proposed experiments)



The Migdal effect in semiconductors can enhance sensitivity to nuclear recoils from sub-GeV dark matter

$$\text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

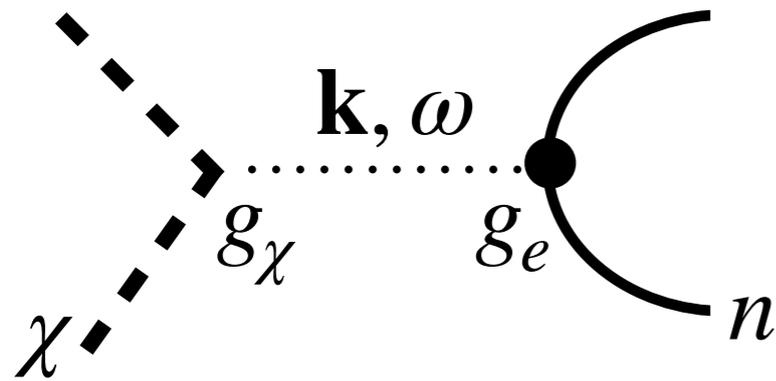
The energy loss function (ELF) in dielectric materials describes response to any electromagnetic probe (Standard Model or DM)

Unifies approach to multiple DM mediators and target materials

First principles calculations accounting for many-body effects

Data-driven and experimental calibration of ELF

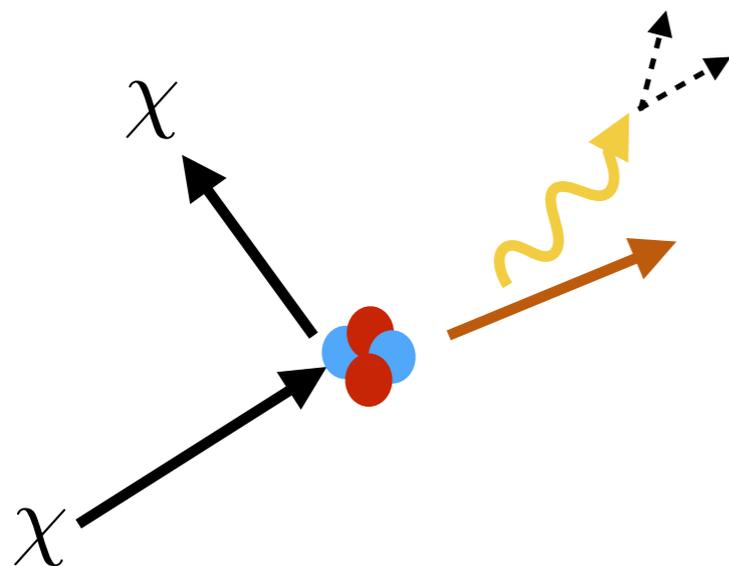
DM-electron scattering



$$\frac{d\sigma}{d^3\mathbf{k}d\omega} \propto \bar{\sigma}_e F_{\text{med}}^2(\mathbf{k}) \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

Screening effects in semiconductors and superconductors

DM-nucleus scattering: the Migdal effect



$$\frac{dP}{d^3\mathbf{k}d\omega} \propto \frac{4\pi\alpha_{em}Z_{\text{ion}}^2}{\omega^4} \frac{|\mathbf{v}_N \cdot \mathbf{k}|^2}{k^2} \text{Im} \left(\frac{-1}{\epsilon(\omega, \mathbf{k})} \right)$$

First derivation & calculation of Migdal effect
in semiconductors